



《风光欣》技术资料

A42

NPN EPITAXIAL SILICON TRANSISTOR

HIGH VOLTAGE TRNSISTOR

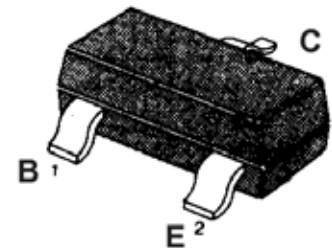
*Collector-Emitter Voltage: $V_{CEO}=300V$

*Collector Dissipation: $P_c(\max)=625mW$

ABSOLUTE MAXIMUM RATINGS($T_A=25$)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	300	V
Collector-Emitter Voltage	V_{CEO}	300	V
Emitter -Base Voltage	V_{EBO}	6	V
Collector Current	I_c	500	mA
Collector Dissipation	P_c	625	mW
Junction Temperature	T_J	150	
Storage Temperature	T_{STG}	-55 ~150	

SOT-23



ELECTRCAL CHARACTERISTICS($T_A=25$)

Characteristic	Symbol	Test Conditions	Min	Max	Unit
Collector-Base Breakdown Voltage	BV_{CBO}	$I_c=100 \mu A, I_E=0$	300		V
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_c=1mA, I_B=0$	300		V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E=100 \mu A, I_c=0$	6		V
Collector Cut-off Current	I_{CBO}	$V_{CB}=200V, I_E=0$		100	nA
Emitter Cut-off Current	I_{EBO}	$V_{BE}=6, I_c=0$		100	nA
*DC Current Gain	H_{FE}	$V_{CE}=10V, I_c=1mA$ $V_{CE}=10V, I_c=10mA$ $V_{CE}=10V, I_c=30mA$	25 40 40		
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_c=20mA, I_B=2mA$		0.5	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_c=20mA, I_B=2mA$		0.9	V
Collector-Base Capacitance	C_{CB}	$V_{CB}=20V, I_E=0, F=1MHZ$		3	pF
Output Gain Bandwidth Product	f_T	$V_{CE}=20V, I_c=10mA$ $f=100KHZ$	50		MHz